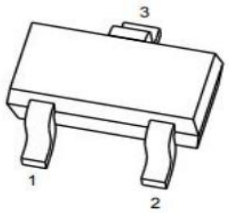
2SC4617 TRANSISTOR(NPN)

FEATURES

- **Low Cob:Cob=2.0pF(Typ)**
- **Complement to 2SA1774**

SOT–523



1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Power Dissipation	150	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃unless otherwise specified)

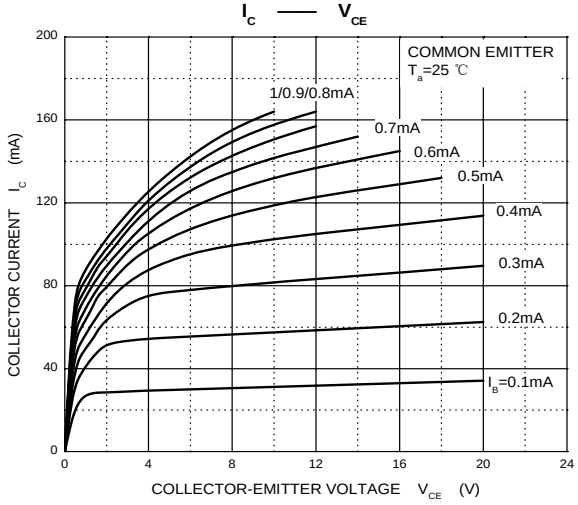
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=50uA, I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=50uA, I_C=0	7			V
Collector cut-off current	I_{CBO}	V_{CB}=60V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=7V, I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=6V, I_C=1mA	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=50mA, I_B=5mA			0.4	V
Transition frequency	f_T	V_{CE}=12V, I_C=2mA, f=100MHz		180		MHz
Collector output capacitance	C_{ob}	V_{CB}=12V, I_E=0, f=1MHz			3.5	pF

CLASSIFICATION OF h_{FE}

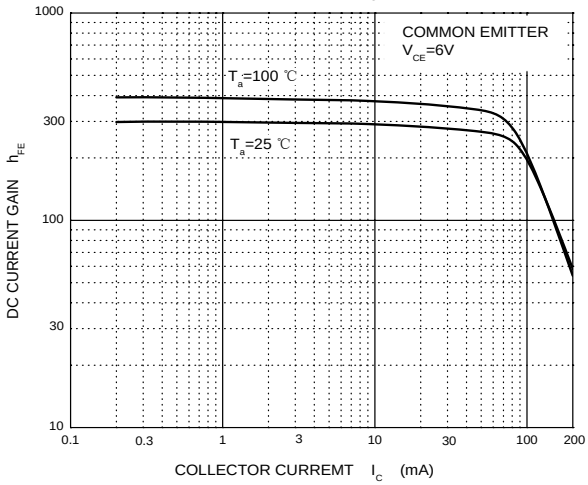
Rank	Q	R	S
Range	120-270	180-390	270-560
Marking	BQ	BR	BS

TYPICAL CHARACTERISTICS

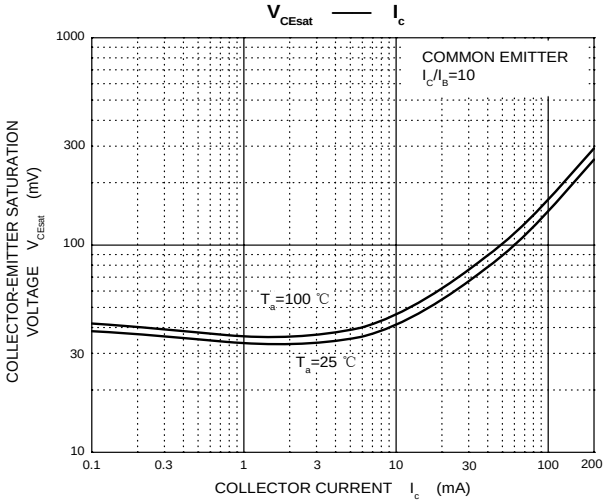
I_C —— V_{CE}



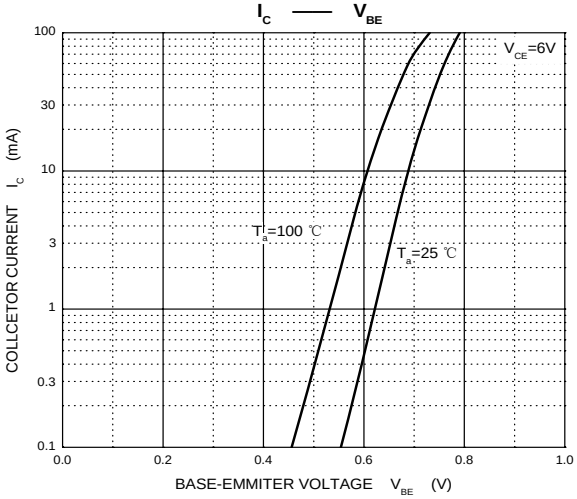
h_{FE} —— I_C



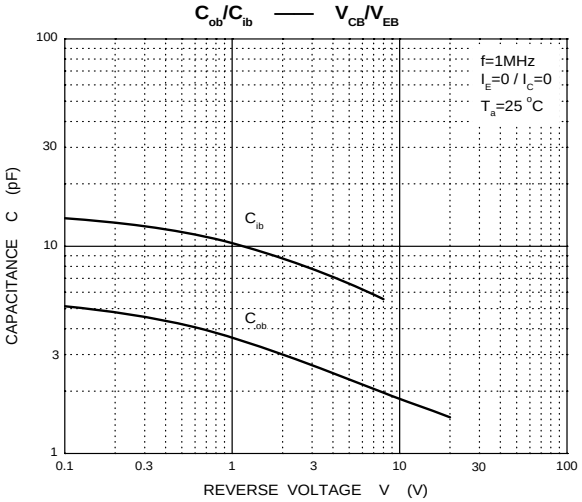
V_{CEsat} —— I_c



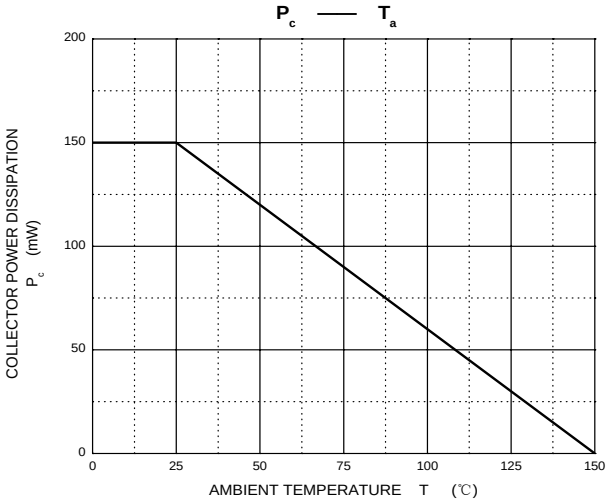
I_C —— V_{BE}



C_{ob}/C_{ib} —— V_{CB}/V_{EB}

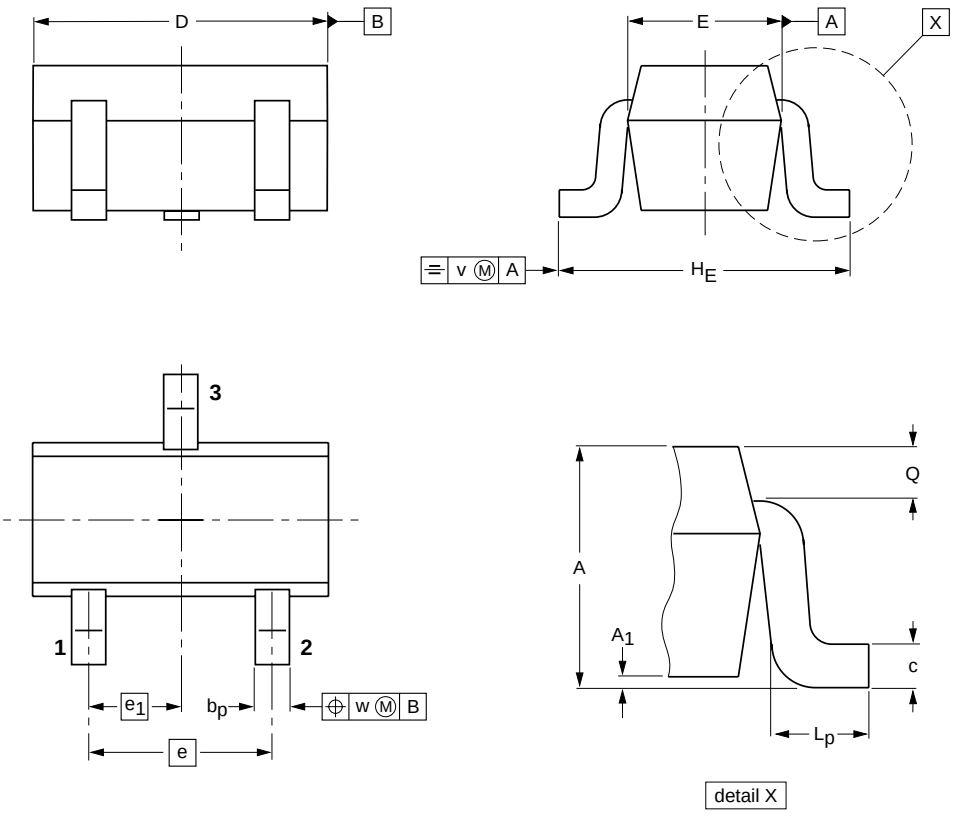


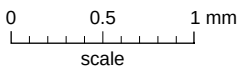
P_c —— T_a



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads SOT-523





DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

单击下面可查看定价，库存，交付和生命周期等信息

>>TWGMC(台湾迪嘉)